

SEMICONDUCTOR STRUCTURE HAVING A COMPENSATED RESISTANCE IN
THE LDD AREA AND METHOD FOR PRODUCING THE SAME

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ABSTRACT

10 A semiconductor structure includes a substrate, a source
area formed in the substrate and a drain area formed in
the substrate and comprising a doping of a first
conductivity type. The drain area includes a first drain
portion with a first doping concentration and a second
drain portion with a second doping concentration, wherein
the first doping concentration is higher than the second
doping concentration. In the second drain portion a first
15 region is formed comprising a doping of a second
conductivity type which is different to the first
conductivity type. Further, a second region is formed in
the substrate below the second drain portion comprising a
doping of the first conductivity type. A channel area is
20 provided in the substrate between the source area and the
second drain portion.